

EAST Search History

L12	12	I11 and kimura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:50
L13	48594	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:52
L14	1348	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:52
L15	165	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode) same (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:53
L16	65	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode) same (tft or (thin adj film adj transistor)) same ((first or second or third or multilayer or multi-layer or multilevel or multi-level))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:59
L17	1	"09505858"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:58
L18	2	"09/505858"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:58
L19	3	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode) same (tft or (thin adj film adj transistor)) same ((first or second or third or multilayer or multi-layer or multilevel or multi-level)) and (scan with (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 07:59

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L20	5	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode) same (tft or (thin adj film adj transistor)) same ((first or second or third or multilayer or multi-layer or multilevel or multi-level)) and (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:01
L21	2	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode) same (tft or (thin adj film adj transistor)) same ((multilayer or multi-layer or multilevel or multi-level)) and (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:00
L22	10	(ti or titanium) same (tin or (titanium near nitride)) same (al or aluminum) same (gate adj electrode) same (tft or (thin adj film adj transistor)) same ((first or second or third or two or three or multilayer or multi-layer or multilevel or multi-level)) and (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:02
L23	5686	(scan or scanning) with (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:02
L24	15	(scan or scanning) with (gate adj electrode) and ((tiN or (titanium adj nitride)) with (concentration or ratio or contain or containing) with nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:03
L25	15	(scan or scanning) with (gate adj electrode) and (((tiN or (titanium adj nitride)) with (concentration or ratio or contain or containing) with nitrogen))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:05
L26	8	(scan or scanning) near10 (connect or connecting or connected) near10 (gate adj electrode) and (((tiN or (titanium adj nitride)) with (concentration or ratio or contain or containing) with nitrogen))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:05

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L27	8	((scan or scanning) near10 (connect or connecting or connected) near10 (gate adj electrode)) and (((tiN or (titanium adj nitride)) with (concentration or ratio or contain or containing) with nitrogen))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/11 08:06
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